

RELIABILITY REPORT
FOR
MAX14826GTG+T
PLASTIC ENCAPSULATED DEVICES

December 8, 2015

MAXIM INTEGRATED

160 RIO ROBLES
SAN JOSE, CA 95134

Approved by
Eric Wright
Quality Assurance
Reliability Engineer

Conclusion

The MAX14826GTG+T successfully met the quality and reliability standards required of all Maxim Integrated products. In addition, Maxim Integrated's continuous reliability monitoring program ensures that all outgoing product will continue to meet Maxim Integrated's quality and reliability standards.

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I. Device Description

A. General

The MAX14826 transceiver is suitable for IO-Link® devices and 24V binary sensors. All specified IO-Link data rates are supported. In IO-Link applications, the transceiver acts as the physical layer interface to a microcontroller running the data-link layer protocol. Additional 24V digital inputs and outputs are provided. Two internal linear regulators generate common sensor and actuator power requirements: 5V and 3.3V. On-board C/Q and DO drivers are independently-configurable for push-pull, high-side (PNP), or low-side (NPN) operation. The device detects the IO-Link C/Q wake-up condition and generates a wake-up signal on the active-low WU/THSD output. The MAX14826 includes a selectable parallel or SPI interface for configuration and monitoring of the drivers. Extensive alarm conditions are detected and communicated through the interrupt outputs and the SPI interface. The device features reverse-polarity, short-circuit, and thermal protection. All power lines are monitored for undervoltage conditions. The C/Q and DO drivers are specified for sinking/sourcing 200mA. The MAX14826 is available in a 4mm x 4mm, 24-pin TQFN package, and is specified over the extended -40°C to +105°C temperature range.

II. Manufacturing Information

A. Description/Function:	IO-Link Device Transceiver
B. Process:	S45
C. Number of Device Transistors:	15024
D. Fabrication Location:	USA
E. Assembly Location:	Taiwan, China, Thailand
F. Date of Initial Production:	September 26, 2014

III. Packaging Information

A. Package Type:	24-pin TQFN 4x4
B. Lead Frame:	Copper
C. Lead Finish:	100% matte Tin
D. Die Attach:	Conductive
E. Bondwire:	Au (1 mil dia.)
F. Mold Material:	Epoxy with silica filler
G. Assembly Diagram:	#05-9000-5741
H. Flammability Rating:	Class UL94-V0
I. Classification of Moisture Sensitivity per JEDEC standard J-STD-020-C	Level 1
J. Single Layer Theta Ja:	48°C/W
K. Single Layer Theta Jc:	2.7°C/W
L. Multi Layer Theta Ja:	36°C/W
M. Multi Layer Theta Jc:	2.7°C/W

IV. Die Information

A. Dimensions:	100X100 mils
B. Passivation:	Si ₃ N ₄ /SiO ₂ (Silicon nitride/ Silicon dioxide)
C. Interconnect:	Al/0.5%Cu with Ti/TiN Barrier
D. Backside Metallization:	None
E. Minimum Metal Width:	Metal1 = 0.5 / Metal2 = 0.6 / Metal3 = 0.6 microns (as drawn)
F. Minimum Metal Spacing:	Metal1 = 0.45 / Metal2 = 0.5 / Metal3 = 0.6 microns (as drawn)
G. Bondpad Dimensions:	
H. Isolation Dielectric:	SiO ₂
I. Die Separation Method:	Wafer Saw

V. Quality Assurance Information

- A. Quality Assurance Contacts: Don Lipps (Manager, Reliability Engineering)
Bryan Preeshl (Vice President of QA)
- B. Outgoing Inspection Level: 0.1% for all electrical parameters guaranteed by the Datasheet.
0.1% for all Visual Defects.
- C. Observed Outgoing Defect Rate: < 50 ppm
- D. Sampling Plan: Mil-Std-105D

VI. Reliability Evaluation

A. Accelerated Life Test

The results of the 135°C biased (static) life test are shown in Table 1. Using these results, the Failure Rate (λ) is calculated as follows:

$$\lambda = \frac{1}{\text{MTTF}} = \frac{1.83}{192 \times 4340 \times 80 \times 2} \quad (\text{Chi square value for MTTF upper limit})$$

(where 4340 = Temperature Acceleration factor assuming an activation energy of 0.8eV)

$$\lambda = 13.7 \times 10^{-9}$$

$$\lambda = 13.7 \text{ F.I.T. (60\% confidence level @ 25°C)}$$

The following failure rate represents data collected from Maxim Integrated's reliability monitor program. Maxim Integrated performs quarterly life test monitors on its processes. This data is published in the Reliability Report found at <http://www.maximintegrated.com/qa/reliability/monitor>. Cumulative monitor data for the S45 Process results in a FIT Rate of 0.49 @ 25°C and 8.49 @ 55°C (0.8 eV, 60% UCL)

B. E.S.D. and Latch-Up Testing

The RV04-0 die type has been found to have all pins able to withstand an HBM transient pulse of +/-1500V per JEDEC JESD22-A114. Latch-Up testing has shown that this device withstands a current of +/-100mA and overvoltage per JEDEC JESD78.

Table 1
Reliability Evaluation Test Results

MAX14826GTG+T

TEST ITEM	TEST CONDITION	FAILURE IDENTIFICATION	SAMPLE SIZE	NUMBER OF FAILURES	COMMENTS
Static Life Test (Note 1)	Ta = 135°C Biased Time = 192 hrs.	DC Parameters & functionality	80	0	

Note 1: Life Test Data may represent plastic DIP qualification lots.